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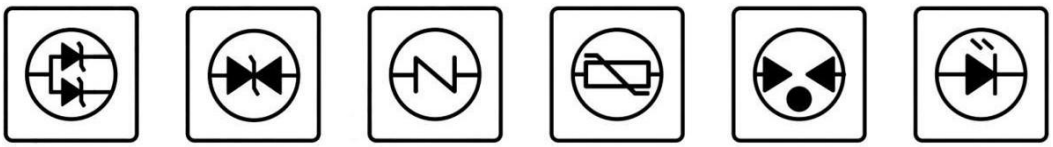
SEMICONDUCTOR



AONR36368-MS

Product specification

Description

The AONR36368-MSuses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V.
This device is suitable for use as a Battery protection or in other Switching application.

Features

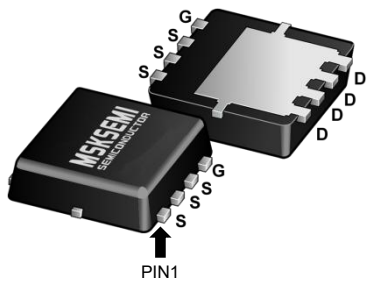
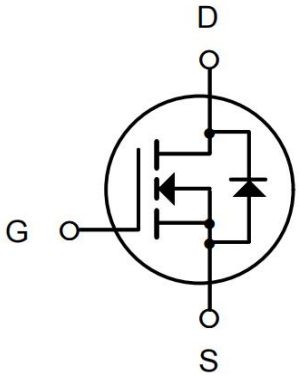
V_{DS} = 30V I_D =60 A

$R_{DS(ON)}$ <8mΩ @ V_{GS}=-10V

Application

- Battery protection
- Load switch
- Uninterruptible power supply

Reference News

PACKAGE OUTLINE	N-Channel MOSFET	Marking
		
DFN3X3-8L		

Absolute Maximum Ratings (TC=25℃ unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	60	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	20	A
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	15	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ 10V[1]	12	A
I_{DM}	Pulsed Drain Current[2]	140	A
EAS	Single Pulse Avalanche Energy[3]	115.2	mJ
I_{AS}	Avalanche Current	48	A
P_D@T_C=25℃	Total Power Dissipation[4]	59	W
P_D@T_A=25℃	Total Power Dissipation[4]	2	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1]	62	℃/ W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	2.1	℃/ W

Electrical Characteristics (TJ=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain- Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.027	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=20A	---	6	8	mΩ
		V_{GS}=4.5V , I_D=10A		7.5	10	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	---	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.8	---	Mv/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=24V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate- Source Leakage Current	V_{GS}= ±20V , V_{DS}=0V	---	---	± 100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=30A	---	43	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.7	---	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=15V , V_{GS}=4.5V , I_D=15A	---	20	---	nC
Q_{gs}	Gate- Source Charge		---	7.6	---	
Q_{gd}	Gate- Drain Charge		---	7.2	---	
$T_{d(on)}$	Turn- On Delay Time	V_{DD}=15V , V_{GS}=10V , R_G=3.3 Ω I_D=15A	---	7.8	---	ns
T_r	Rise Time		---	15	---	
$T_{d(off)}$	Turn- Off Delay Time		---	37.3	---	
T_f	Fall Time		---	10.6	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	2295	---	pF
C_{oss}	Output Capacitance		---	267	---	
C_{rss}	Reverse Transfer Capacitance		---	210	---	
I_S	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	40	A
I_{SM}	Pulsed Source Current[2,6]		---	---	140	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1	V

Diode Characteristics

Note :

1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3 .The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=34A

4.The power dissipation is limited by 150℃ junction temperature

5 .The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

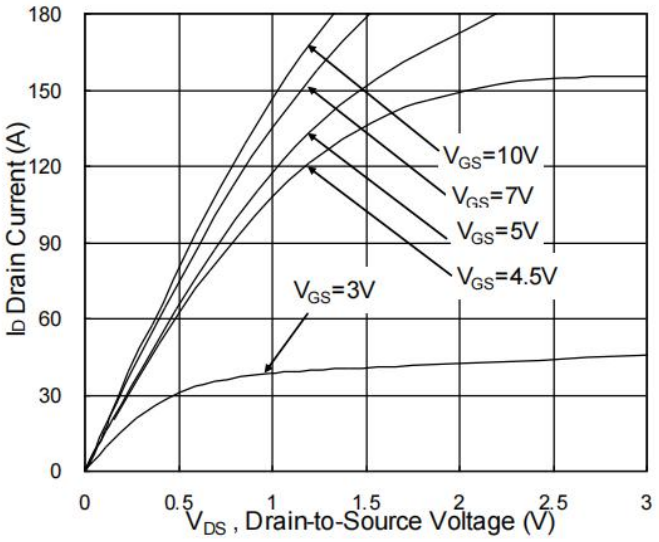


Fig.1 Typical Output Characteristics

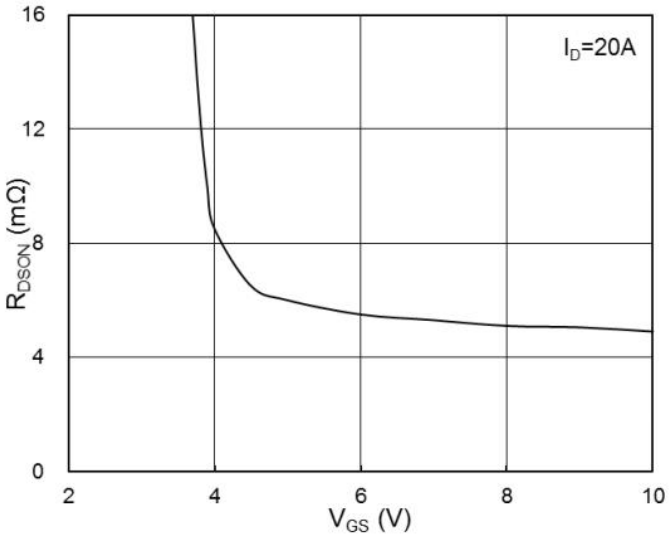


Fig.2 On-Resistance vs. G-S Voltage

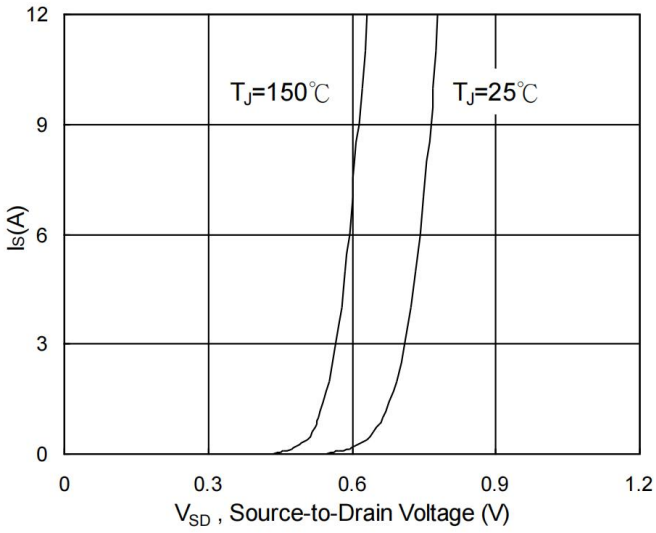


Fig.3 Forward Characteristics of Reverse

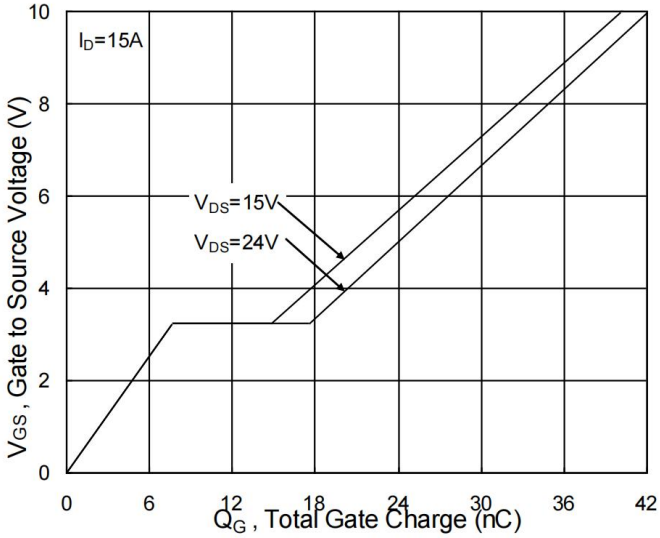


Fig.4 Gate-Charge Characteristics

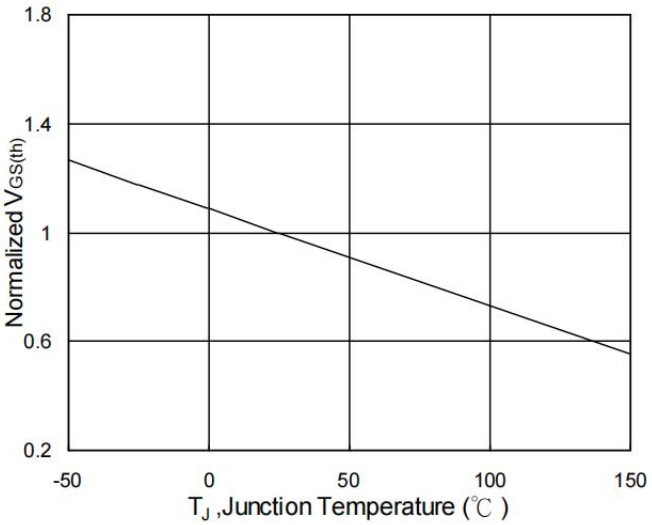


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

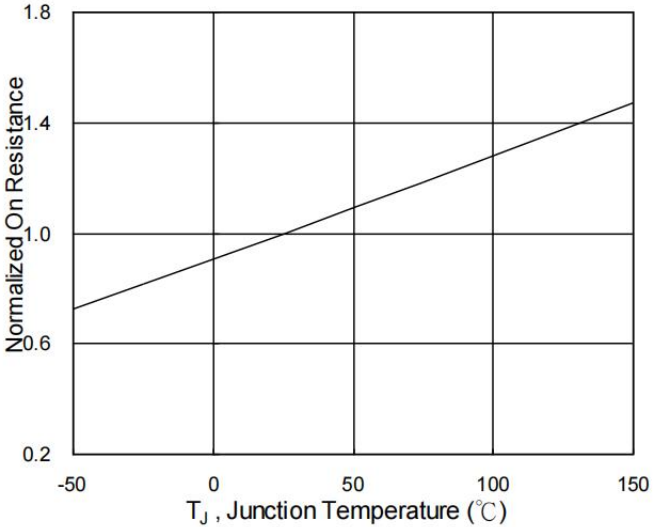


Fig.6 Normalized R_{DSON} vs. T_J

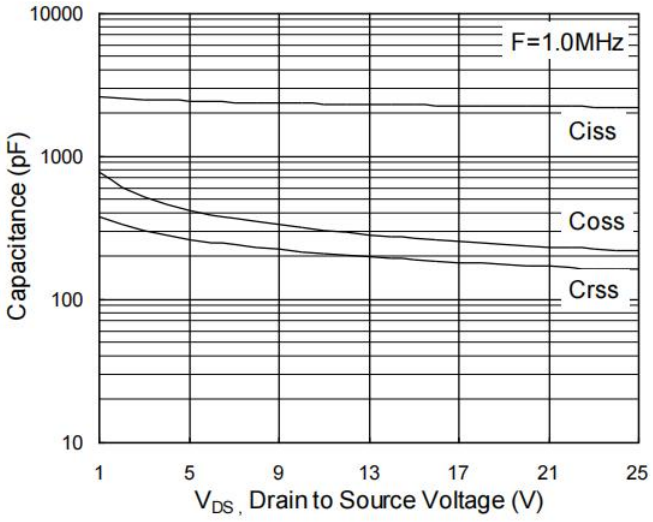


Fig.7 Capacitance

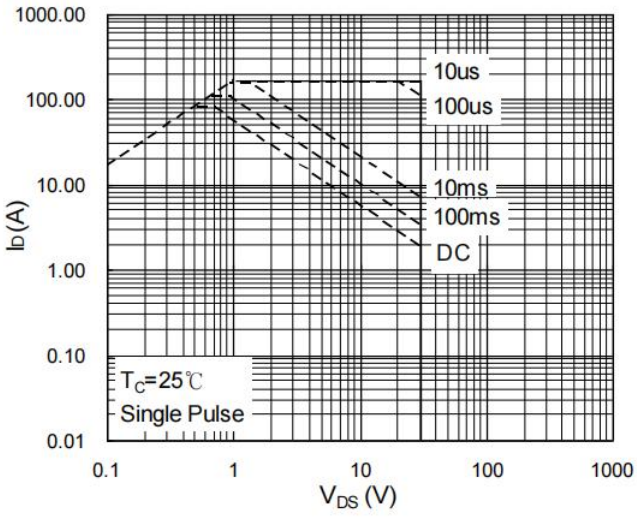


Fig.8 Safe Operating Area

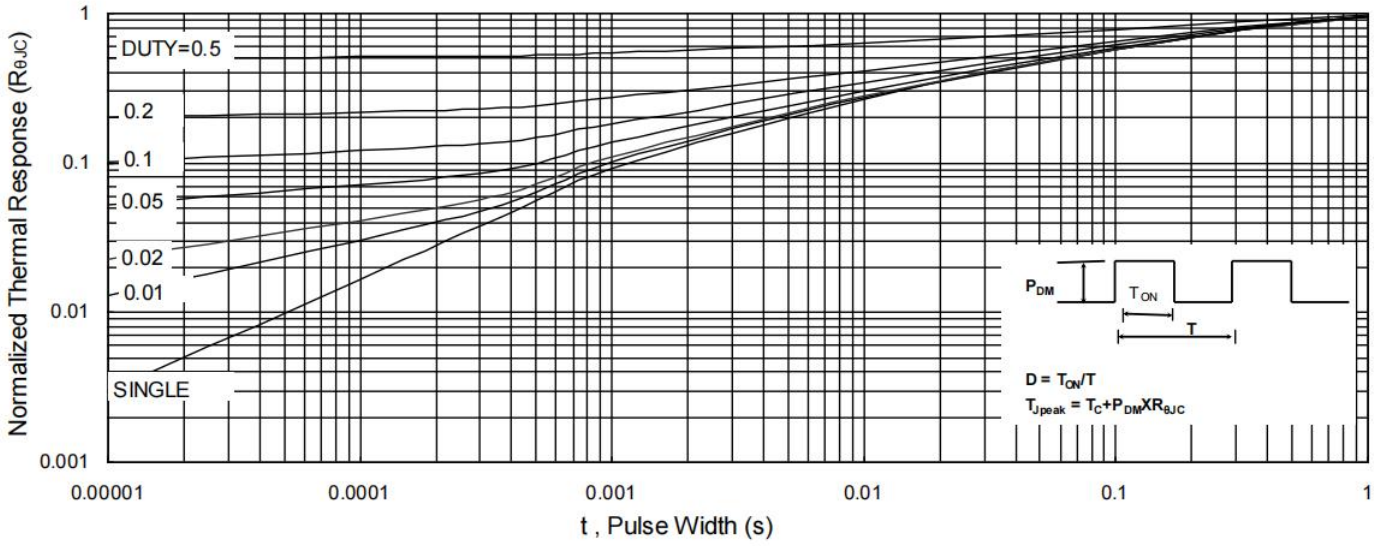


Fig.9 Normalized Maximum Transient Thermal Impedance

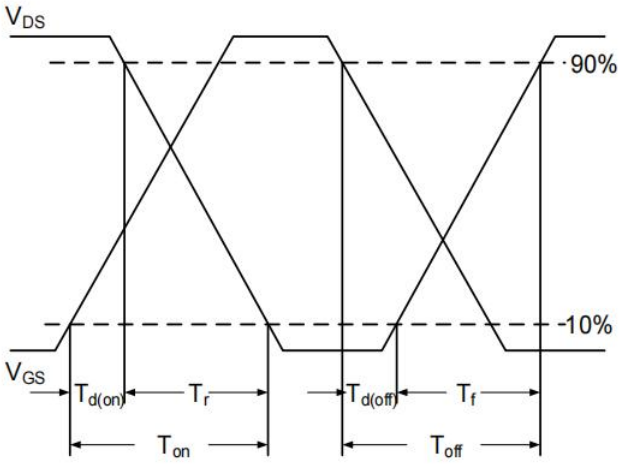


Fig.10 Switching Time Waveform

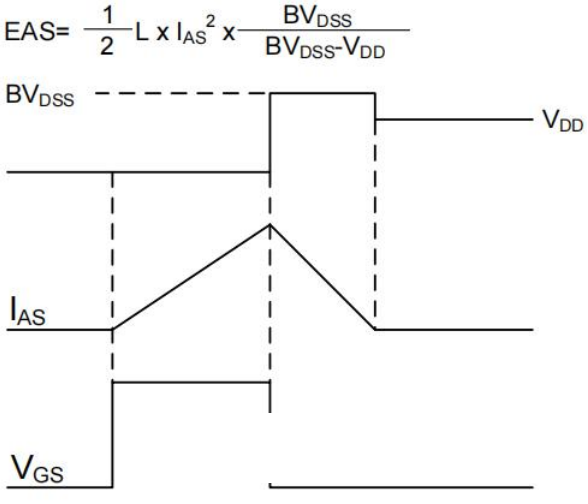
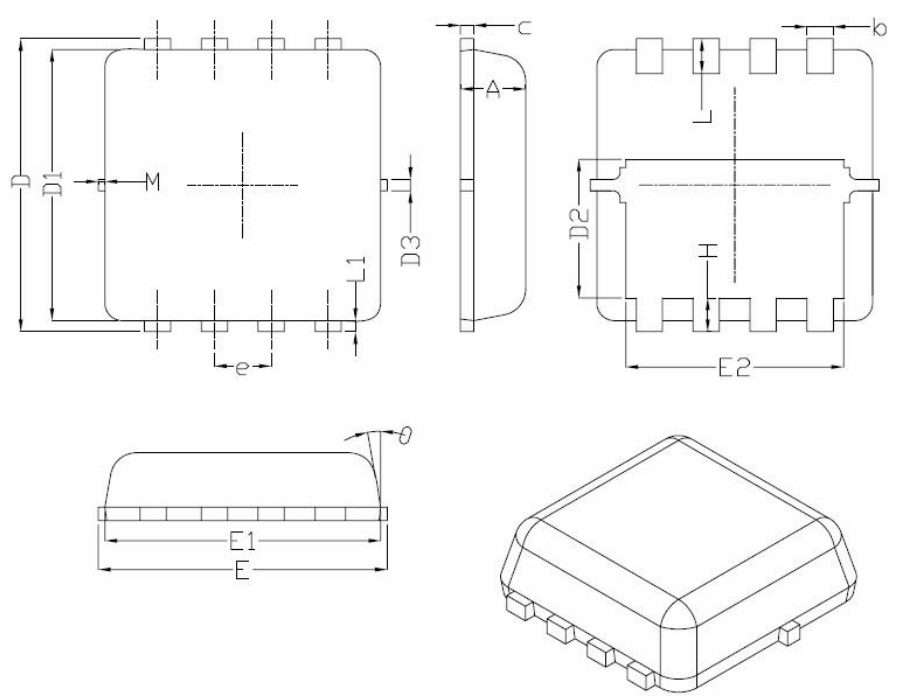


Fig.11 Unclamped Inductive Switching Waveform

DFN3X3-8L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°

REEL SPECIFICATION

P/N	PKG	QTY
AONR36368-MS	DFN3X3-8L	5000

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